

## **DHG30I600PA**

preliminary

 $V_{RRM} = 600 V$ 

 $I_{FAV} = 30 A$ 

 $t_{rr}$  = 40 ns

High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

**Sonic Fast Recovery Diode** 

Part number

**DHG30I600PA** 



Backside: cathode



### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode
- Turn-on loss in the commutating switch

### **Applications:**

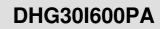
- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

### Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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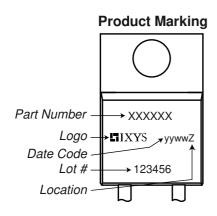
Fast Diode					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V <sub>RSM</sub>	max. non-repetitive reverse blockir	ng voltage	$T_{VJ} = 25^{\circ}C$			600	V	
V <sub>RRM</sub>	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			600	V	
I <sub>R</sub>	reverse current, drain current	$V_R = 600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			50	μΑ	
		$V_R = 600 \text{ V}$	$T_{VJ} = 125^{\circ}C$			2	mΑ	
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 30 A	$T_{VJ} = 25^{\circ}C$			2.27	V	
		$I_F = 60 \text{ A}$				3.14	٧	
		I <sub>F</sub> = 30 A	T <sub>VJ</sub> = 125°C			2.24	V	
		$I_F = 60 \text{ A}$				3.23	٧	
I <sub>FAV</sub>	average forward current	$T_C = 85^{\circ}C$	T <sub>VJ</sub> = 150°C			30	Α	
		rectangular d = 0.5						
V <sub>F0</sub>	threshold voltage		$T_{VJ} = 150$ °C			1.17	V	
r <sub>F</sub>	slope resistance	ss calculation only				32	mΩ	
R <sub>thJC</sub>	thermal resistance junction to case	;				0.7	K/W	
R <sub>thCH</sub>	thermal resistance case to heatsin	k			0.5		K/W	
P <sub>tot</sub>	total power dissipation		$T_{C} = 25^{\circ}C$			180	W	
I <sub>FSM</sub>	max. forward surge current	$t = 10 \text{ ms}$ ; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			200	Α	
C¹	junction capacitance	$V_R = 400  \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		16		pF	
I <sub>RM</sub>	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		13		Α	
		$I_F = 30 \text{ A}; V_R = 300 \text{ V}$	$T_{VJ} = 125$ °C		17		Α	
t <sub>rr</sub>	reverse recovery time	$I_F = 30 \text{ A}; V_R = 300 \text{ V}$ -di <sub>F</sub> /dt = 600 A/µs	$T_{VJ} = 25 ^{\circ}\text{C}$		40		ns	
	)	1	$T_{VJ} = 125$ °C		60		ns	



# **DHG30I600PA**

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Package TO-220				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I <sub>RMS</sub>	RMS current	per terminal			35	Α	
T <sub>VJ</sub>	virtual junction temperature		-55		150	°C	
T <sub>op</sub>	operation temperature		-55		125	°C	
T <sub>stg</sub>	storage temperature		-55		150	°C	
Weight				2		g	
M <sub>D</sub>	mounting torque		0.4		0.6	Nm	
$F_c$	mounting force with clip		20		60	N	



### Part description

D = Diode

H = Sonic Fast Recovery Diode

G = extreme fast

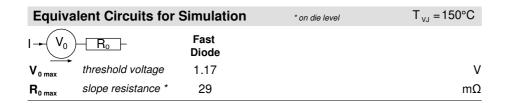
30 = Current Rating [A] I = Single Diode

600 = Reverse Voltage [V]

PA = TO-220AC (2)

Ore	dering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Sta	andard	DHG30I600PA	DHG30I600PA	Tube	50	504019

Similar Part	Package	Voltage class
DHG30I600HA	TO-247AD (2)	600
DHG30IM600PC	TO-263AB (D2Pak) (2)	600

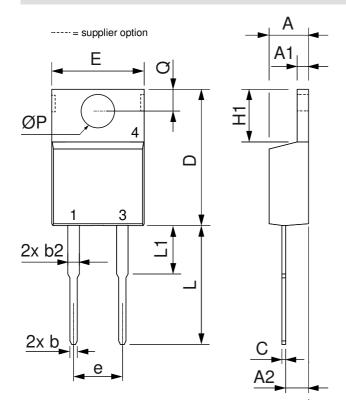






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### Outlines TO-220



Dim.	Millimeter		Incl	nes
	Min.	Max.	Min.	Max.
Α	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
С	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
е	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125





### **Fast Diode**

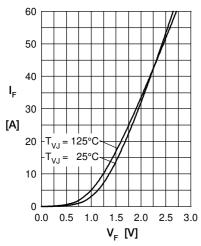


Fig. 1 Typ. Forward current versus V<sub>F</sub>

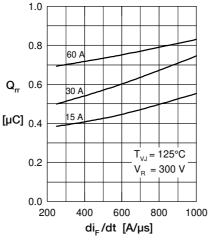


Fig. 2 Typ. reverse recov. charge  $Q_{rr}$  versus di/dt

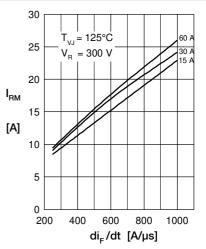


Fig. 3 Typ. peak reverse current  $I_{\rm RM}$  versus di/dt

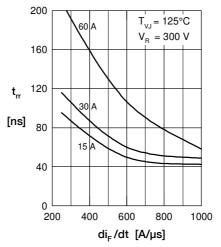
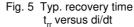
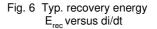


Fig. 4 Dynamic parameters  $Q_{rr}$ ,  $I_{RM}$  versus  $T_{VJ}$ 





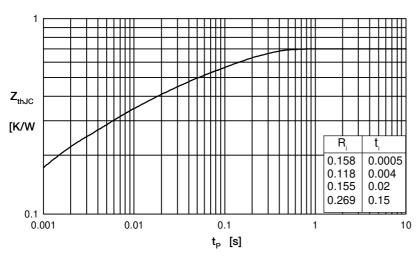


Fig. 7 Typ. transient thermal impedance junction to case

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